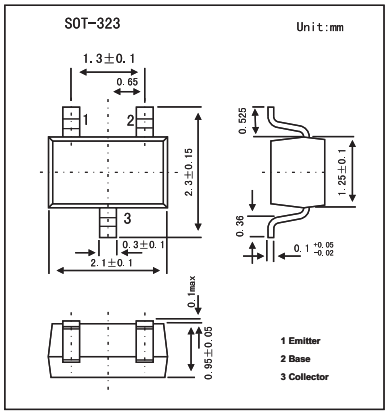
PNP General Purpose Transistors

KC860W(BC860W)



■ Features

- ●Low current (max. 100 mA)
- ●Low voltage (max. 45 V).

■ Absolute Maximum Ratings Ta = 25℃

Parameter	Symbol	Rating	Unit
Collector-Base Voltage	V_{CBO}	-50	V
Collector-Emitter Voltage	V_{CEO}	-45	V
Emitter-Base Voltage	V_{EBO}	-5	V
Collector Current DC	I_C	-100	mA
Peak collector current	I_{CM}	-200	mA
Peak base current	I_{BM}	-200	mA
Power Dissipation	P_D	200	mW
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	625	K/W
Operating and Storage Junction Temperature Range	T_J, T_{stg}	-65 to +150	℃

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■ Electrical Characteristics Ta = 25℃

Parameter		Symbol	Testconditons	Min	Typ	Max	Unit
Collector-Cutoff Current		I_{CBO}	V_{CB} =- 30 V, I_E = 0			-15	nA
			V_{CB} =- 30 V, I_E = 0, T_A = 150℃			-4	μA
Emitter- cutoff current		I_{EBO}	I_C=0,V_{EB}=-5V			-100	nA
DC Current Gain	KC860W	h_{FE}	I_C = -2.0 mA, V_{CE} = -5.0 V	220		800	
	KC860BW			220		475	
	KC860CW			420		800	
Collector-Emitter Saturation Voltage		$V_{CE(sat)}$	I_C = -10 mA, I_B =- 0.5 mA			-300	mV
			I_C = -100 mA, I_B =- 5.0 mA			-650	mV
Base-Emitter Voltage		V_{BE}	I_C = -2mA, I_B=-5A	-600		-750	m V
			I_C = -10 mA, I_B=-5A			-820	m V
Collector capacitance		C_c	I_E = i_e = 0; V_{CB} = -10 V; f = 1 MHz			5	pF
Emitter capacitance		C_e	I_C = i_c = 0; V_{EB} = -500 mV; f = 1 MHz		10		pF
Noise figure		F	I_C = -200 μA; V_{CE} = -5 V; R_S = 2 kΩ;f = 10 Hz to 15.7 kHz			4	dB
			I_C=-200 μA; V_{CE} = -5 V; R_S = 2 kΩ;f = 1 kHz; B = 200 Hz			4	dB
Transition frequency		f_T	I_C = -10 mA; V_{CE} = -5 V; f = 100 MHz	100			MHz

■ Marking

NO.	KC860W	KC860BW	KC860CW
Marking	4H	4F	4G